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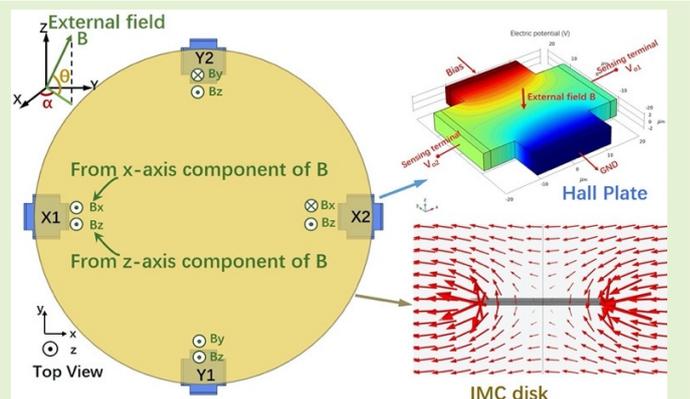
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# Modelling of Three-Axis Hall Effect Sensors based on Integrated Magnetic Concentrator

Hua Fan, *Member, IEEE*, Sujie Li, Vahid Nabaei, *Member, IEEE*, Quanyuan Feng, *Senior Member, IEEE*, and Hadi Heidari, *Senior Member, IEEE*

**Abstract**—In this paper, we develop computational model to analyze the magnetic concentrating effect of integrated magnetic concentrator (IMC) on surrounding external magnetic field. We present an IMC-based three-axis Hall sensor model that enables to measure both inclination angles and absolute strength of a random external magnetic field. An IMC changes surrounding parallel magnetic components into perpendicular components, and therefore allows the horizontal Hall plates to measure both the strength and inclination angles of parallel external magnetic fields. We develop a finite element method (FEM) based model in COMSOL Multiphysics for the three-axis Hall sensor. Key factors influencing IMC's magnetic concentrating effect, including material property and sensor structure, are investigated and discussed using the developed model. Comparing to traditional IMC-based three-axis angular sensors, a reference permanent magnet is no longer needed in the sensor. A measurement accuracy of 0.8 and 1.2 degrees are achieved respectively for the angles of  $\alpha$  and  $\theta$  of external magnetic field.

**Index Terms**—finite element method, Hall effect, integrated magnetic concentrator, magnetic concentrating effect, three-axis sensor



## I. INTRODUCTION

MAGNETIC sensor has been an indispensable element in many systems and instruments, such as automobiles, consumer electronics, and medical devices. So far there have

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H. Fan and S. Li are with the School of Electronic Science and Engineering, University of Electronic Science and Technology of China, Chengdu 610054, China. (e-mail: [fanhua7531@163.com](mailto:fanhua7531@163.com), [lsujie123@126.com](mailto:lsujie123@126.com))

Quanyuan Feng is with the School of Information Science and Technology, Southwest Jiaotong University, Chengdu 611756, China. (e-mail: [fengquanyuan@163.com](mailto:fengquanyuan@163.com))

V. Nabaei and H. Heidari are with Microelectronics Lab, James Watt School of Engineering, University of Glasgow, G12 8QQ Glasgow, United Kingdom (e-mail: [vahid.nabaei@glasgow.ac.uk](mailto:vahid.nabaei@glasgow.ac.uk), [hadi.heidari@glasgow.ac.uk](mailto:hadi.heidari@glasgow.ac.uk))

been many types of magnetic sensors that have been popular in the market. Hall sensors maintains the largest market share because of their low cost, high stability, broad measurement range and great compatibility with COMS technology [1]–[4]. The fundamentals and modelling methods of Hall plate has been already discussed in plenty of research works, and Hall plates of different biasing, different materials, and different structure have been presented [5]–[10]. Horizontal Hall plate measures magnetic components perpendicular to Hall plate plane and is widely popular due to the simple structure. However, the main drawback of traditional horizontal Hall plates is that they are not able to sense magnetic components parallel to Hall plate plane. Many efforts have been devoted to make horizontal Hall plates capable of sensing 3-axis magnetic components. One of the most popular solutions is having three Hall plates orthogonally aligned to measure components in each axis respectively. A three axis Hall effect sensors realized by positioning three horizontal Hall plates on three faces of a non-magnetic material cube has been developed [11]. This solution has been improved in the context of accuracy by using three pairs of two Hall plates [12]. Other approaches include combining a horizontal Hall plate and two pairs of vertical Hall sensors to measure z-axis and x,y-axis respectively [13–14]. These typical solutions have the advantage that each axis is measured independently. However, the unique placement of multiple Hall plates sets high requirement for IC manufacturing technology. The utilization of integrated magnetic concentrator

(IMC) allows the measurement of 3-axis magnetic components with Hall plates in the same plane. Two-axis shifting angle in the IMC plane has been measured by IMC based CMOS Hall angular sensor presented in [15] but shifting angle in z-axis won't be measured [15]. An IMC changes both the directions and strength of a surrounding external magnetic field. At the edge of an IMC, the parallel component of an external magnetic field is changed into the perpendicular direction, hence it becomes possible for horizontal Hall plates to measure magnetic components in all directions. A three-axis CMOS Hall sensor with IMC has been developed that can measure the inclination angles of magnetic field, but the measurement requires a permanent magnet with one end fixed [16]–[18]. Reference [19] mentioned the magnetic saturation effect of the magnetic flux concentrator that may produces nonlinearity error, and presented an analogous three-axis Hall sensor that also measures inclination angles of a fixed permanent magnet [19].

This paper presents an IMC-based three-axis Hall sensor that consists of an IMC and four Horizontal Hall plates. A FEM model is presented to simulate the performance of the three-axis Hall sensor. This paper studies amplification effect of disk-shaped IMC on external magnetic field as the value of IMC's amplification coefficient. Different shapes of IMC could also significantly influence the magnetic concentrating effect and therefore sensitivity of the three-axis Hall sensor. Several unique shapes have been designed, such as a combination five octagonal rings IMC presented in [20]. The main focus of this paper is put on the optimization of disk-shaped IMC's amplification effect, as well as relevant influencing factors. Multiple simulations are conducted to determine the design of specific sensor parameters. An IMC-based three-axis sensor with optimized structure is presented in the end. Unlike the IMC-based three-axis sensors mentioned above, a permanent magnet is no longer needed for the measurement. Both inclination angles and absolute strength of an external magnetic field can be measured by involving IMC's amplification coefficient in the measurement.

The structure of this paper is organized as follows: Section II discusses the fundamental of the three-axis Hall sensor and presents a 3D model of sensor in COMSOL Multiphysics. Section III investigates factors that influence the sensor performance and discusses the simulation results. Finally, Conclusions are drawn in Section IV.

## II. STRUCTURE AND MODELLING OF THREE-AXIS HALL SENSOR

### A. Modelling of Hall plates and IMC

First, a 3D geometry of a single cross-shape horizontal Hall plate has been developed in COMSOL Multiphysics. This model of single Hall plate is used in following simulation of the three-axis sensor. In the model, the Hall plate length is  $40\ \mu\text{m}$  with the thickness of  $5\ \mu\text{m}$ . A cross-shape is adopted for better sensitivity. The Hall plate model was built under physics "Electric Current" in COMSOL. Finite element analysis divides the model into lots of small elements and computing them respectively. Relevant boundary conditions such as

Maxwell's Equations are applied to the model [7][9]. By adding a bias voltage or current on two opposite terminals of Hall plate and applying an external magnetic field, a voltage difference proportional to the strength of perpendicular magnetic components can be seen at the other two terminals. The simulation result of a single horizontal Hall plate is shown in Fig. 1. To maximize the voltage-related sensitivity, we reduced cross-shape Hall plate finger width to  $22\ \mu\text{m}$ , with width-to-length ratio of 0.55, based on the simulation results of sweeping Hall plate finger length from 0 to  $20\ \mu\text{m}$ , as shown in Fig. 2. Four identical Hall plates are needed for a three-axis sensor.

IMC allows horizontal Hall plate to detect magnetic components which are parallel to its plane. Fig 3 (a) illustrates the influence of an IMC, where the lines surrounding IMC represent external magnetic flux. It can be seen from Fig 3 (a) that, at the edge of the IMC, the magnetic flux of an originally horizontal external magnetic field is transformed into the almost

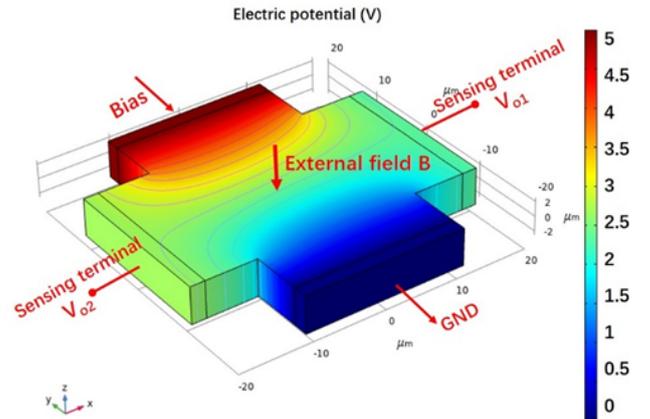


Fig. 1. Cross-shape geometry and 3D model of horizontal Hall plate in COMSOL Multiphysics. A voltage difference on sensing terminals can be clearly seen as sensor biased by 5V voltage.

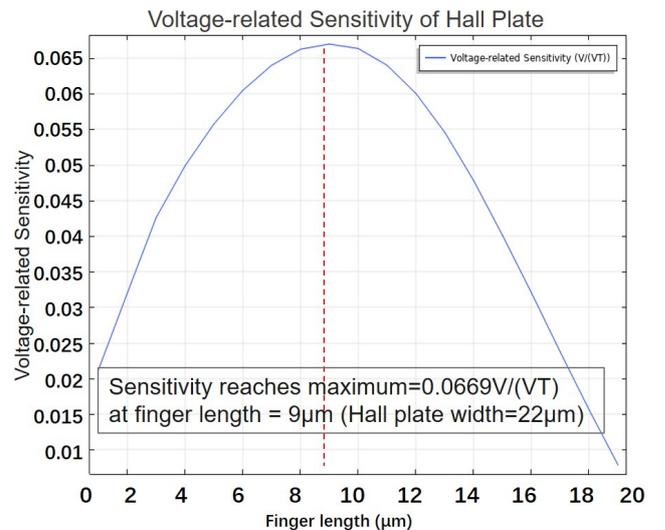


Fig. 2. Voltage-related sensitivity of Hall plate at geometries of different finger length. Best sensitivity of  $0.0669\text{V}/\text{VT}$  is achieved at a Hall plate width of  $22\ \mu\text{m}$ .

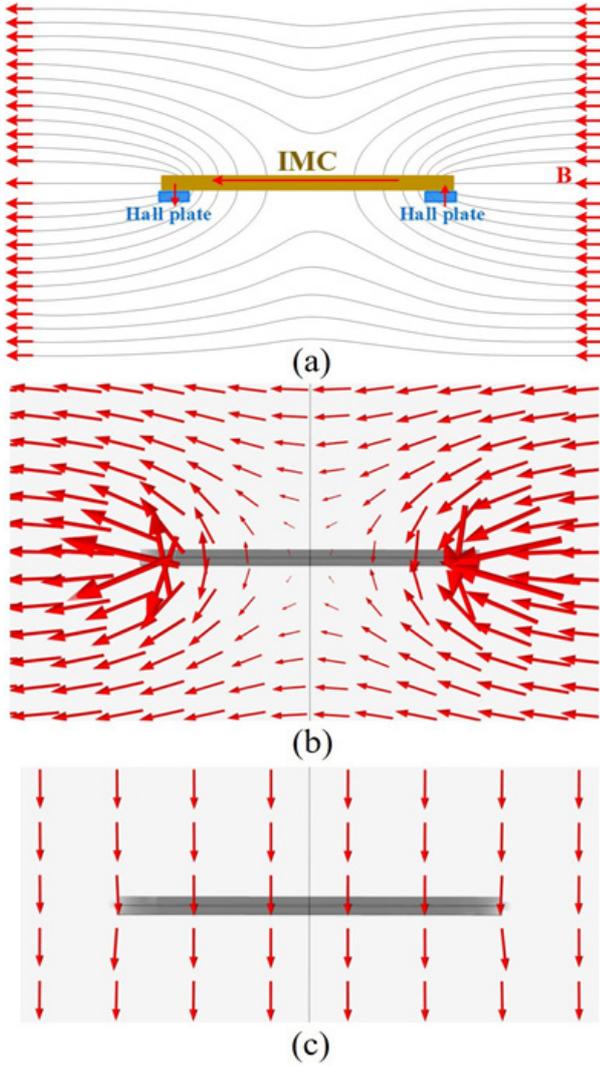


Fig. 3. IMC's influence on surrounding magnetic flux. (a) IMC's magnetic concentrating effect on parallel external magnetic field. (b) Simulation of IMC in a parallel magnetic field in COMSOL. (c) Simulation of IMC in a perpendicular magnetic field in COMSOL.

vertical direction. Ferromagnetic material is often used to make IMCs because of its high permeability. An ideal IMC is usually expected to be infinite long and extremely thin. Disk shape of IMC has the advantage of keeping its effect uniform for external magnetic field from all directions. Fig. 3 (b) and Fig. 3 (c) show the front view of COMSOL simulation results of putting a thin disk-shaped IMC with a permeability of 10000 into a parallel magnetic field and a perpendicular magnetic field respectively. The rectangular object in the figures is the IMC and the red arrows represent both the strength and directions of the magnetic flux surrounding the IMC. The length of the red arrows is proportional to the magnetic flux density. It can be seen from Fig. 3 (b) that the parallel external magnetic field has been mostly transformed into perpendicular direction and its strength has increased at the edge of IMC. This means the IMC has very strong influence on the horizontal magnetic field, on both strength and direction. However, it has only very limited influence on the vertical magnetic field as shown in Fig. 3 (c). IMC's amplifying effects on parallel external magnetic components can be represented by an amplification coefficient  $C_{xy}$ , the value which usually ranges from 1 to 10.

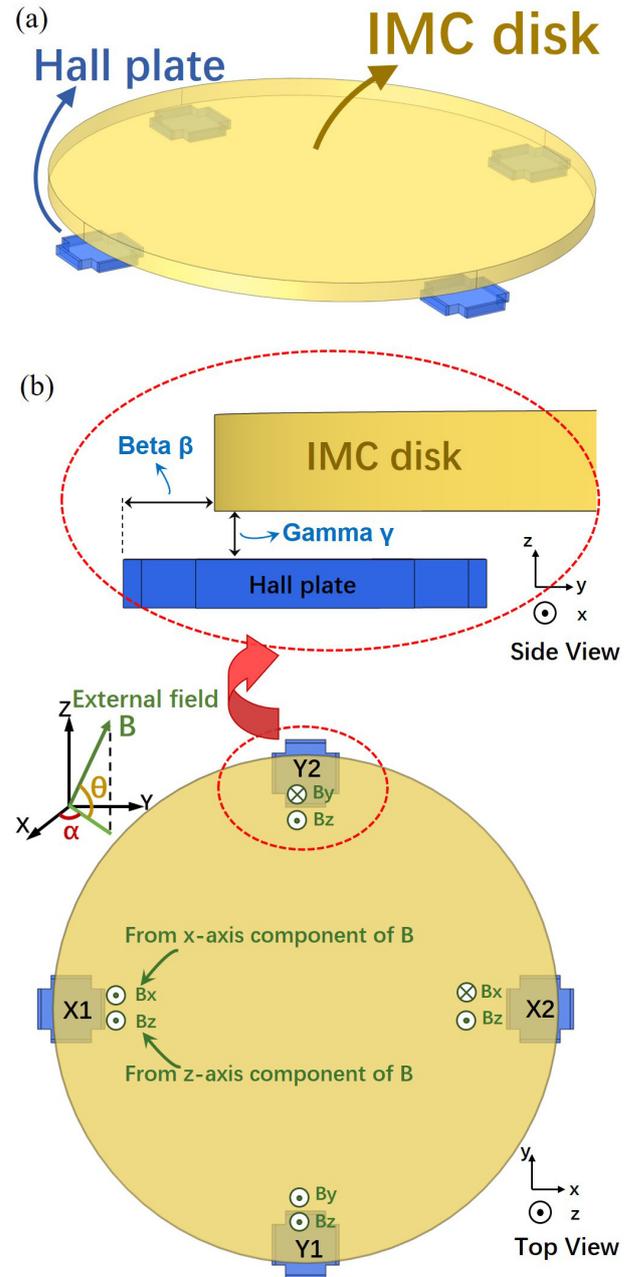


Fig. 4. (a) Structure of the three-axis Hall sensor. (b) Side and top view of the three-axis Hall sensor. An external magnetic field  $B$  is applied to the three-axis sensor and sensed by 4 Hall plates with different directions.

IMC's slight influence on perpendicular external magnetic components can be represented by an amplification coefficient  $C_z$ , and the value of  $C_z$  is usually around 1.

### B. THREE-AXIS HALL SENSOR

The IMC-based three-axis Hall sensor, shown in Fig. 4, consists of an IMC disk and four horizontal Hall plates. Fig. 4 (a) is the essential parts of the COMSOL model geometry of the IMC-based three-axis Hall sensor. The models of Hall plates and IMC disk are already respectively built in COMSOL. Four Hall plates are evenly distributed under the edge of IMC, so that

both the x-axis and y-axis components of an external magnetic field will be transformed to z-axis direction by IMC and will therefore be detected by the horizontal Hall plates, as illustrated in Fig. 3 (a). Four Hall plates are used in the sensor and this enable to distinguish contribution from x-axis, y-axis and z-axis magnetic components. Fig. 4 (b) shows the side and top views of the three-axis Hall sensor. Because of IMC's magnetic concentrating effect, as shown in Fig. 3 (b), Hall plates X1 and X2 sense upward and downward perpendicular magnetic flux contributed by x-axis external magnetic components, respectively. As illustrated in Fig. 4 (b), for such an external magnetic field B, Hall plates X1 and X2 detect a sum of z-axis magnetic component and x-axis magnetic component, while the measurement results of X1 and X2 are not affected by y-axis magnetic component. In addition, the x-axis magnetic components detected by X1 and X2 are in opposite directions. Also, Hall plates Y1 and Y2 detect a sum of z-axis magnetic component and y-axis magnetic component (in opposite directions). In addition, the sensed x-axis and y-axis components are strengthened by IMC with an amplification coefficient of  $C_{xy}$ , the influencing factor of which will be discussed here. In a three-axis Hall sensor, the Hall voltages of four voltage-biased horizontal Hall plates are expressed by:

$$V_{HallX1} = S_v V_{bias} (B_z C_z + B_x C_{xy}) \quad (1)$$

$$V_{HallX2} = S_v V_{bias} (B_z C_z - B_x C_{xy}) \quad (2)$$

$$V_{HallY1} = S_v V_{bias} (B_z C_z + B_y C_{xy}) \quad (3)$$

$$V_{HallY2} = S_v V_{bias} (B_z C_z - B_y C_{xy}) \quad (4)$$

where  $S_v$  is the voltage-related sensitivity of the Hall plates.  $V_{bias}$  is biasing voltage on Hall plates.  $B_x, B_y, B_z$  represents the x, y, and z axis components of the external magnetic field respectively.  $C_z$  is the IMC amplification coefficient for vertical magnetic field components.  $C_{xy}$  is the IMC amplification coefficient for parallel magnetic field components.

The sensitivity of the three-axis sensor is primarily dependent on Hall plates' sensitivity and the IMC amplification coefficient. The sensitivity for the three axis components is:

$$S_x = \frac{V_{HallX1} - V_{HallX2}}{V_{bias} B_x} = 2S_v C_{xy} \quad (5)$$

$$S_y = \frac{V_{HallY1} - V_{HallY2}}{V_{bias} B_y} = 2S_v C_{xy} \quad (6)$$

$$S_z = \frac{V_{HallX1} + V_{HallX2}}{V_{bias} B_x} = \frac{V_{HallY1} + V_{HallY2}}{V_{bias} B_y} = 2S_v C_z \quad (7)$$

For an external magnetic field, the direction of which is shown as the green arrow in Fig. 4, both the angle  $\theta$  between the direction of magnetic field B and the position of x-y plane, and the angle  $\alpha$  between the x-axis line and the projection of magnetic field B on the x-y plane can be measured by the three-axis Hall sensor. The x, y, and z axis components of external magnetic field B are respectively described as:

$$B_x = B \cos \theta \cos \alpha \quad (8)$$

$$B_y = B \cos \theta \sin \alpha \quad (9)$$

$$B_z = B \sin \theta \quad (10)$$

Therefore, the specific value of angle  $\alpha$  and angle  $\theta$  can then be obtained from IMC amplification coefficient  $C_z, C_{xy}$  and measured Hall voltages of four Hall plates:

$$\frac{V_{HallY1} - V_{HallY2}}{V_{HallX1} - V_{HallX2}} = \frac{B_y}{B_x} = \tan \alpha \quad (11)$$

$$\begin{aligned} & \frac{C_{xy}}{C_z} \frac{V_{HallX1} + V_{HallX2}}{\sqrt{(V_{HallX1} - V_{HallX2})^2 + (V_{HallY1} - V_{HallY2})^2}} \\ &= \frac{B_z}{\sqrt{B_x^2 + B_y^2}} = \tan \theta \end{aligned} \quad (12)$$

The measurement of inclination angle  $\alpha$  only depends on the output voltages of the four Hall plates. The measurement of inclination angle  $\theta$  involves not only the Hall voltages, but also the value of amplification coefficients  $C_{xy}$  and  $C_z$ . For a settled structure of three-axis sensor, the value of  $C_{xy}$  and  $C_z$  are invariant during measuring process and can be measured in advance.

Apart from inclination angle of external magnetic field, the three-axis Hall sensor is also capable of measuring the absolute strength of external magnetic field B:

$$B = \frac{B_z}{\sin \theta} = \frac{V_{HallX1} + V_{HallX2}}{2S_v V_{bias} C_z \sin \theta} \quad (13)$$

The measurement accuracy of external magnetic field strength depends on the accuracy of the measured inclination angles as well as the accuracy of adopted Hall plates.

### III. ANALYSIS OF KEY FACTORS AND SENSOR PERFORMANCE

#### A. Factors influencing IMC Amplification Coefficient

IMC structure and positions of Hall plates are key factors that influence IMC's magnetic concentrating effect. Amplification coefficient of perpendicular field  $C_z$  does not vary too much and usually floats around 1, however, amplification coefficient of parallel field  $C_{xy}$  is largely influenced by the variation of these factors. A larger value of IMC amplification coefficient results in a greater sensitivity of the sensor. We focus in this paper on the improvement of IMC amplification coefficient, and therefore to find an optimized sensor structure.

A desired three-axis sensor model is already finally determined. So in the following simulations, one key factor is designed as variable each time while other parameters are chosen to be proper values and remain constant. In the final sensor model, the bar length and thickness of single Hall plates are 40  $\mu\text{m}$  and 5  $\mu\text{m}$ , respectively. The permeability of IMC material is 20000 and the IMC length and thickness are 300  $\mu\text{m}$  and 5  $\mu\text{m}$ , respectively. The vertical distance between IMC and Hall plates, i.e. Gamma  $\gamma$  in Fig. 4 (b), is 5  $\mu\text{m}$ . The horizontal distance between IMC and Hall plates, i.e. Beta  $\beta$  in Fig. 4 (b), is 10  $\mu\text{m}$ . The magnetic concentrating effect of IMC is highly dependent on its material. Ferromagnetic material is a commonly adopted IMC material because of its high permeability. However, materials' permeability cannot be

infinite. To determine a proper relative permeability value for IMC’s magnetic concentrating effect, we calculated amplification coefficients of parallel magnetic components  $C_{xy}$  for different material relative permeability and simulation results shown in Fig. 5 verify the theory that the higher the IMC material permeability is, the better the magnetic concentrating effect is. The amplification coefficient  $C_{xy}$  increases rapidly while the permeability is low, and tends to converge to a maximum value. As shown in the results, the amplification coefficient is almost saturated with the fixed structure when the relative permeability of IMC material increased to 20000, and the corresponding amplification coefficient is 2.335. Thus, a relative permeability value over 20000 is optimal for IMC material.

The shape of IMC, which also strongly influences IMC’s magnetic concentrating effect, would need to be determined. Disk shape is popular in IMC design, as it provides a uniform concentrating effect on external magnetic field from all directions. IMC’s effective length in the direction of parallel external magnetic components largely affects the magnetic concentrating effect. Simulations are conducted to find the IMC amplification coefficient of parallel field  $C_{xy}$  under different IMC length. Fig. 6 shows the simulation results of sweeping

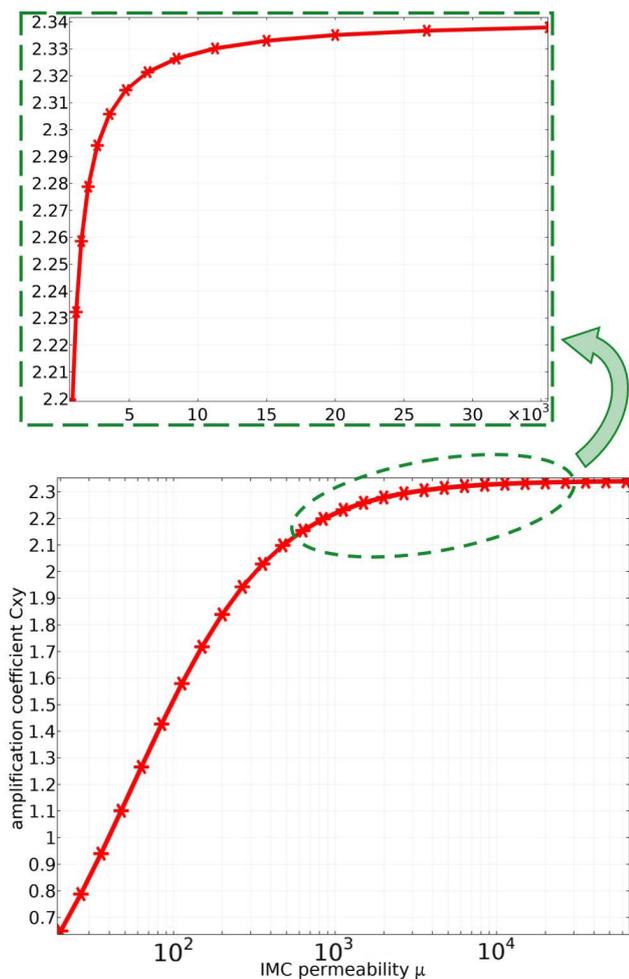


Fig. 5. (a) Influence of material permeability on amplification coefficient. Amplification coefficient  $C_{xy}$  increases as permeability increases, and tends to be stable after IMC permeability reaches 20000.

IMC length. It can be seen from the results that the x, y-axis amplification coefficient  $C_{xy}$  increases as the IMC length increases, which means a larger IMC length enhances the magnetic concentrating effect. However, increasing IMC length leads to an increase of chip area. According to the simulation results, an IMC length value of 300  $\mu\text{m}$  is chosen to be the design parameter as the trade-off in the case.

The influence of IMC thickness is then simulated, and the results are shown in Fig. 7. Smaller IMC heights can lead to stronger magnetic concentrating effect. In addition, when the IMC thickness decreased to a very small value, which means the IMC disk is thin enough, decreasing IMC thickness no longer significantly improves magnetic concentrating effect. Thus, an IMC thickness of 5  $\mu\text{m}$  is determined in the final sensor design. Once material and geometry of IMC disk are determined, the Hall cross position with respect to IMC should be optimized. An initial idea is that the position Hall cross should be close to the edges of IMC disk, where vertical components of external magnetic field achieve a maximum value, see Fig. 3 (b). Two key parameters, the vertical distance

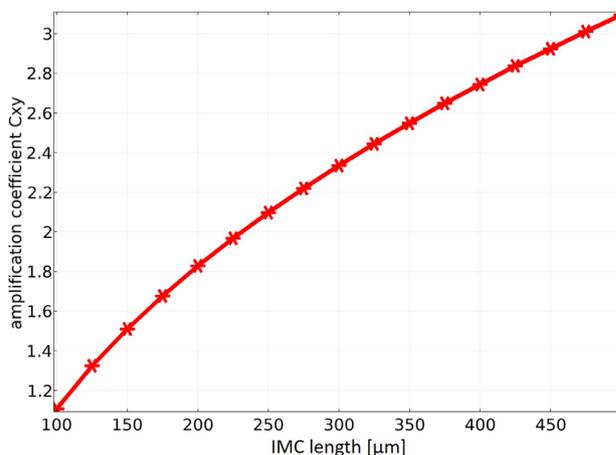


Fig. 6. Influence of IMC length on amplification coefficient. Increasing IMC length leads to larger amplification coefficient  $C_{xy}$ , but at a cost of larger chip area.

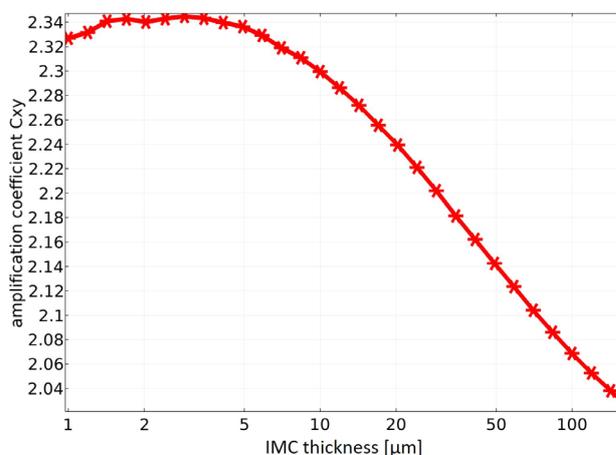
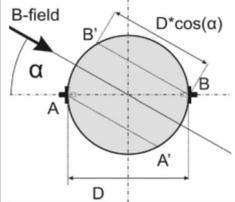
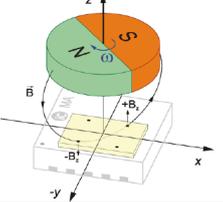
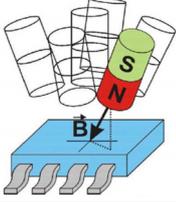
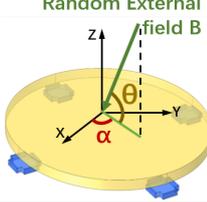


Fig. 7. Influence of IMC thickness on amplification coefficient. An ideal IMC is expected to be thinner than 5  $\mu\text{m}$ . Thicker IMC tend to have weaker magnetic concentrating effect.

TABLE I  
COMPARISON OF IMC-BASED THREE-AXIS SENSOR

Reference	Popovic <i>et al.</i>		Schott <i>et al.</i> [16]	This work
	[15]	[19]		
Structure				
Measurement range	2D (x-y axis)	3D (x-y-z axis)	3D (x-y-z axis)	3D (x-y-z axis)
components	IMC + 4 Hall plates	IMC + 4 Hall plates + permanent magnet	IMC + 4 Hall plates + permanent magnet	IMC + 4 Hall plates
Amplification factor $C_{xy}$	Not involved	Not involved	2.0 (according to results)	2.335
Amplification factor $C_z$	Not involved (z-axis not measured)	Not involved	Neglected	1.035

Gamma  $\gamma$  and horizontal distance Beta  $\beta$  between IMC and Hall cross, are used to fix the position of IMC and Hall plates. The simulation results of the influence of vertical distance Gamma  $\gamma$  are shown in Fig. 8. Just like the initial estimate, as the vertical distance Gamma  $\gamma$  becomes larger the transformed perpendicular components sensed by Hall plates become weaker. To improve the sensitivity of the three-axis sensor, the four Hall plates are designed to be  $5 \mu\text{m}$  under IMC edges.

Horizontal distance between IMC and Hall crosses, as the horizontal distance  $\beta$  indicated in Fig. 4 (b), is a key factor that significantly influence both the amplification coefficient of parallel magnetic components  $C_{xy}$  and the amplification coefficient of perpendicular magnetic components  $C_z$ . Fig. 9 shows the relations between  $C_{xy}$  and  $\beta$ . It can be seen that the amplification coefficient  $C_{xy}$  tends to be 0 when the Hall plates are placed horizontally far from the IMC.  $C_{xy}$  also reduces when Hall plates are placed closely under the IMC center, and this can be explained by the presented results in Fig. 3 (b) that the external magnetic field is weakest around IMC center. In addition, we obtain maximum  $C_{xy}$  when  $\beta$  is  $10 \mu\text{m}$ , which represents the position for highest sensitivity. However, according to the obtained simulation results for relation between  $C_z$  and  $\beta$  in Fig. 10, the  $C_z$  also can be increased when  $\beta$

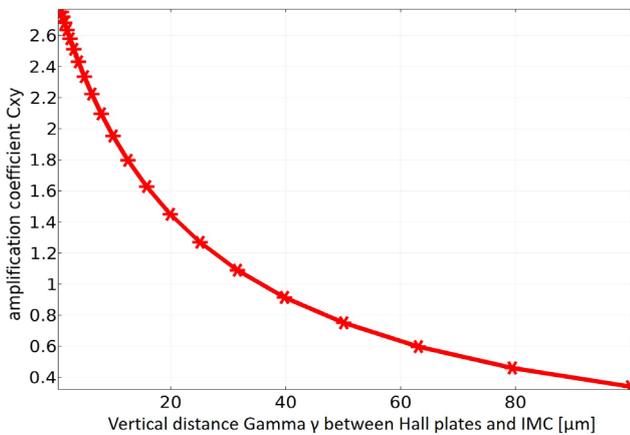


Fig. 8. Influence of vertical distance  $\gamma$ . The closer the Hall plates are placed under the IMC, the stronger the magnetic components sensed by Hall plates are.

is  $10 \mu\text{m}$ . At the point of  $\beta = 27 \mu\text{m}$ , the value of  $C_z$  is 0 and the IMC's influence on vertical magnetic components can be ignored to further reduce deviation. As a trade-off between sensitivity and accuracy,  $\beta = 10 \mu\text{m}$  and  $\gamma = 5 \mu\text{m}$  is the final design, which results in amplification coefficient  $C_{xy} = 2.335$  and  $C_z = 1.035$ .

### B. Design and Simulation of Three-axis Hall Sensor

For the determined material and structure of three-axis sensor, the amplification coefficient  $C_{xy} = 2.335$  and  $C_z = 1.035$

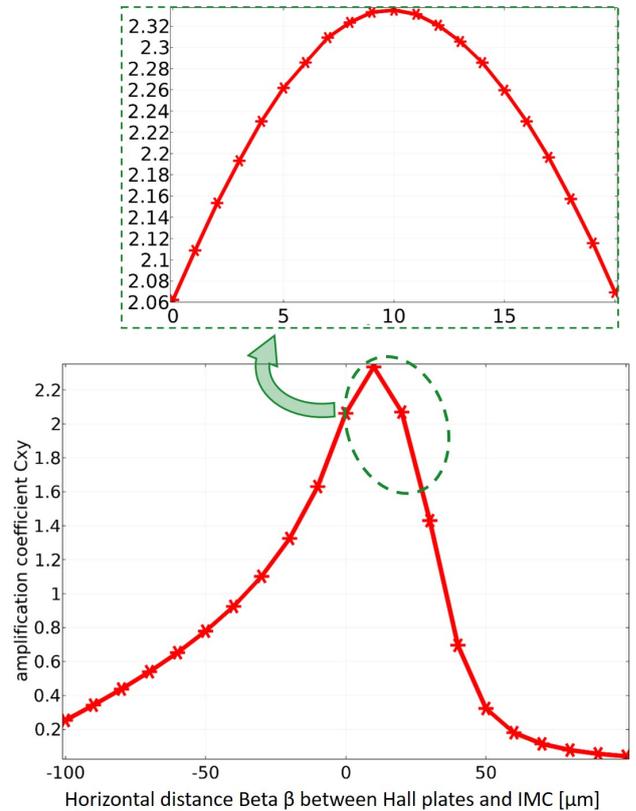


Fig. 9. Influence of horizontal distance  $\beta$  on  $C_{xy}$ . The magnetic concentrating effect is weak both in centre of or far away from the IMC. A maximum amplification coefficient  $C_{xy}$  is achieved when  $\beta$  is  $10 \mu\text{m}$ .

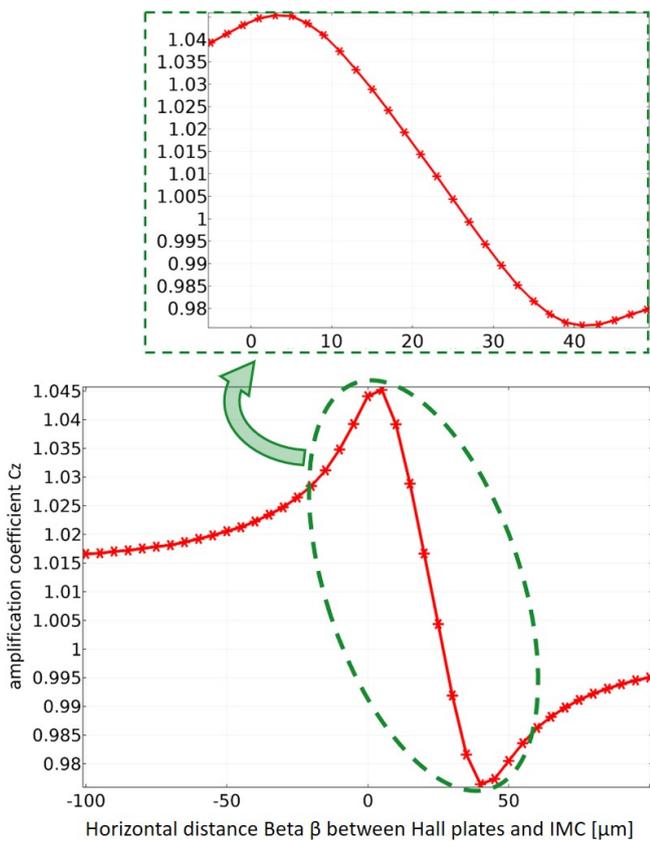


Fig. 10. Influence of horizontal distance  $\beta$  on  $C_z$ . The amplification coefficient  $C_z$  is 1.035 when  $\beta$  is 10  $\mu\text{m}$ . IMC's effect on perpendicular magnetic field can be neglected when  $\beta$  is 27  $\mu\text{m}$ .

can be used to realize the measurement of inclination angle and magnetic field strength. An external magnetic field  $B$  is applied on the three-axis sensor model in COMSOL. The direction of external magnetic field changes in the form of varying angles  $\alpha$  and  $\theta$  (see Fig. 4). Plugging the values of amplification coefficient  $C_{xy} = 2.335$ ,  $C_z = 1.035$ , and the measured Hall voltages from 4 Hall plates into (11) and (12), both accurate angles and absolute strength of the external magnetic field can therefore be measured.

The simulation of three-axis angular sensor is conducted in COMSOL and the results of inclination angle  $\alpha$  and  $\theta$  are shown in Figs. 11 (a) and (b), respectively. It can be seen, the measurement accuracy of angles of  $\alpha$  and  $\theta$  are 0.8 and 1.2 degree, respectively. The absolute strength of external magnetic field  $B$  can also be obtained through (13). The accuracy of absolute strength is significantly influenced by performance of the four Hall plates. Hall plates with high accuracy being adopted in the design could lead to high accuracy of the measurement of magnetic field strength. Therefore, by taking into consideration the specific value of magnetic amplification coefficients  $C_{xy}$  and  $C_z$ , both the strength and inclination angles of 3-axis external magnetic fields can be measured with only horizontal Hall plates.

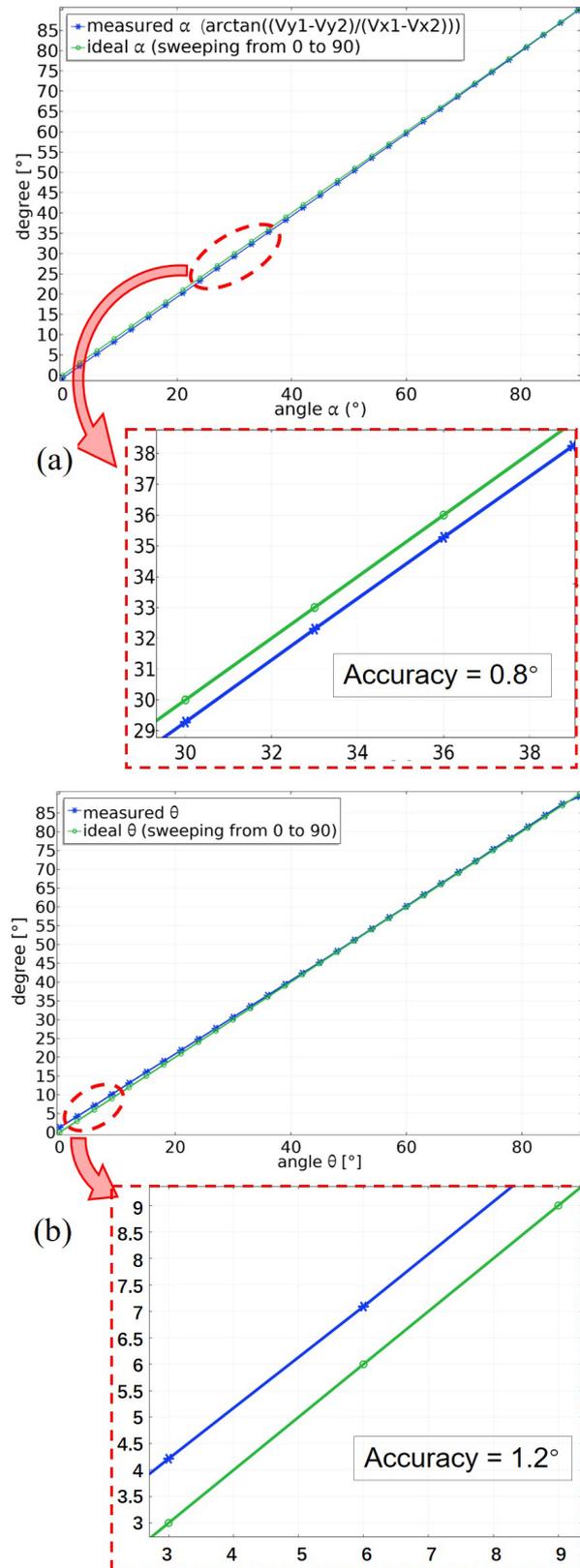


Fig. 11. (a) Accuracy of 0.8 degree can be achieved for the measurement of angle  $\alpha$ . (b) Accuracy of 1.2 degree can be achieved for the measurement of angle  $\theta$ .

#### IV. CONCLUSION

This paper aims to study IMC's magnetic concentrating effect in an IMC-based three-axis Hall sensor. Influence of geometric factors and IMC permeability on the IMC's magnetic concentrating effect are firstly investigated and compared to find optimal parameters for sensor design. TABLE I shows the comparison with state-of-the-arts. An improvement in amplification factor is achieved by optimizing sensor structure. The amplification factor of parallel magnetic components has achieved a value of 2.335. The effect of IMC's magnetic concentrating effect on perpendicular component has been taken into consideration to improve the measurement accuracy. In addition, through the usage of IMC's magnetic amplification coefficient  $C_{xy}$  and  $C_z$ , the three-axis Hall sensor no longer need a reference external magnet and shows great significance comparing to traditional IMC-based magnetic sensors. A three-axis Hall sensor 3D model in COMSOL Multiphysics is also presented in this paper. An accuracy of 1.2 degree has been achieved for the three-axis angular sensor in the case. In addition, more customized sensor design can be investigated and applied to the proposed FEM model in the future, such as novel shapes of IMC and different arrangement of Hall plates. With this being said, this paper aims to provide a new perspective as well as a general method for researchers to optimize relevant designs.

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**Hua Fan** (M'16) was born in Ziyang, Sichuan, China, in 1981. She received the B.S. degree in communications engineering and the M.S. degree in Computer science and technology, both from Southwest Jiaotong University, Chengdu, China, in 2003 and 2006, respectively. She received the Ph.D. degree from Tsinghua University, Beijing, in July 2013. From September 2013 to June 2016, she was an assistant professor of University of Electronic Science and Technology of China, from July 2016 to present, she is an associate professor of University of

Electronic Science and Technology of China, Chengdu, China. Her research interests include low-power, high-speed and high-resolution A/D converter designs. From March 2015 to March 2016, she joined the Integrated Microsystem (IMS) research group in the department of electrical computer and biomedical engineering at University of Pavia in Italy as a post-doc under the supervision of Professor Franco Maloberti. She has been the recipient of a number of awards including the Best Oral Presentation Award from the IEEE Asia Pacific Conference on Circuit and Systems (APCCAS) in 2018, China Scholarship Council (CSC) support in 2015, etc. She has authored over 50 articles in peer reviewed journals (e.g. *IEEE Trans. Circuits and Systems I*, *IEEE Trans. Circuits and Systems II*, and *IEEE Access*, etc.) and in international conferences.



**Sujie Li** was born in Changsha, Hunan, China, in 1995. He received the B.S. degree in Automation engineering from University of Electronic Science and Technology of China, Chengdu, China in 2017. From August 2017 to present, he is a master student of both KTH Royal Institute of Technology (Kungliga tekniska hogskolan), Stockholm, Sweden and University of Electronic Science and Technology of China, Chengdu, China. His main research interest is horizontal Hall sensor.



**Vahid Nabaei** hold PhD from the Polytechnic University of Turin, Italy, in Electrical Engineering. He has been mainly working on finite element modeling of different magnetic sensors at National Metrological Institute of Turin, Italy. His PhD thesis was in the framework of the European Metrological Research Programme (EMRP) Project, MetMag.

After his PhD, he was an assistant professor at the Department of Electrical Engineering at Azad University, Iran. Now he is Research Assistant at University of Glasgow, in Microelectronics Lab (meLAB) group, working on a part of a

5-year €8.4 million EU H2020 FET-Proactive funded project. His current research activity is device modelling for flexible microelectronics. He has worked as an author/co-author of top-tier journals in modelling and simulation of magnetic devices for different sensing applications.



**Quanyuan Feng** (M'06–SM'08) received the M.S. degree in microelectronics and solid electronics from the University of Electronic Science and Technology of China, Chengdu, China, in 1991, and the Ph.D. degree in electromagnetic field and microwave technology from Southwest Jiaotong University, Chengdu, in 2000. He is currently the Head of the Institute of Microelectronics, Southwest Jiaotong University. In recent five years, he has authored more than 500 papers such as the

IEEE Transactions on Power Electronics, IEEE Transactions on Antennas and Propagation, the IEEE Transactions on Microwave Theory and Techniques, and the IEEE Antennas and Wireless Propagation Letters, among which more than 300 were registered by SCI and EI. His current research interests include integrated circuits design, RFID technology, embedded system, wireless communications, antennas and propagation, microwave and millimeter-wave technology, smart information processing, electromagnetic compatibility, and RF/microwave devices and materials. Dr. Feng has been honored as the "Excellent Expert" and the "Leader of Science and Technology" of Sichuan Province owing to his outstanding contribution.



**Hadi Heidari** (S'11–M'15–SM'17) is an Assistant Professor (Lecturer) in the James Watt School of Engineering at the University of Glasgow, United Kingdom. His Microelectronics Lab (meLAB) consists of 3 postdoctoral researchers and 8 PhD students, conducts pioneering research on magnetoelectronics and integrated microelectronics design for wearable and implantable devices. He has authored over 150 articles in peer reviewed journals (e.g. IEEE Solid-State Circuits Journal, Trans. Circuits and Systems I and IEEE Trans. Electron Devices)

and in international conferences. He has organized several conferences, workshops and special sessions, e.g. he is founder chairs of UK-China Emerging Technology (UCET) workshop, UK Circuits and Systems (UKCAS) workshop, and member of organizing committee of SENSORS'17-'18, BioCAS'18 and PRIME'2019. He is an IEEE Senior Member, an Editor for the Elsevier Microelectronics Journal and lead Guest Editor for four journal special issues. He is member of the IEEE Circuits and Systems Society Board of Governors (BoG), and Member-at-Large IEEE Sensors Council. He has received several best paper awards from IEEE international conferences including ISCAS'14, PRIME'14, ISSCC'16, and travel scholarship from IEEE NGCAS'17. He has grant portfolio of +£1 million funded by major research councils and funding organizations including European Commission, UK's EPSRC, Royal Society and Scottish Funding Council.